Supplementary Materials

Device Performance Limit and Negative Capacitance of Monolayer GeSe and GeTe Tunneling Field Effect Transistor

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Figure S1. Transfer characteristics of the ML (a) GeSe and (b) GeTe TFET with the source doping concentration $N_S$ of 1, 0.5, $0.1 \times 10^{13}$ cm$^{-2}$ at a supply voltage of 0.74 V. The drain doping concentration $N_D$ is fixed at $5 \times 10^{13}$ cm$^{-2}$.